

	6inch N Type DSP Silicon Prime Wafers			
1	Growth Method: CZ			
2	Wafer Diameter: 150 +/- 0.3mm			
3	Wafer Thickness: 675 +/- 15µm			
4	Wafer Surface Orientation: <100> +/- 0.1Degree			
5	Dopant: N Type, Phosphorus			
6	Carbon Content (max): 0.5 ppma			
7	Oxygen Content (max): 28 +/- 5 ppma or better			
8	Resistivity: 3 to 5 Ohm cm			
9	Radial Resistivity Variation (max.): 8 percent			
10	Dislocation Density: 100 per cm2 max			
11	Bow/Warpage: 40 microns max			
12	TTV (max): 5 microns			
13	Taper (max): 10 microns			
14	Primary Flat Length & Orientation: 57.5 +/- 2.5 mm, {110} +/- 1Degree as per SEMI standard			
15	Secondary Flat: No Secondary Flat			
16	Front & Back Surface: Double Side Mirror Polished			
17	Maximum particles of size >= 0.3 microns: 30			
18	Appearance: No Particles, Scratches, Haze, Edge Chips should be visible under bright collimated light			
19	Packaging: Should be vacuum sealed in Class 10 environment in double layer packing. Wafers should be shipped in Fluorware ORION TWO wafer shippers or equivalent makes made			

	from ultra clean polypropylene			
20	Qty Required for 6inch N Type DSP Silicon Prime Wafers: 250Nos			